E50A2CBS, E50A2CBR

STACK SILICON DIFFUSED DIODE

ALTERNATOR DIODE FOR AUTOMOTIVE APPLICATION.

FEATURES

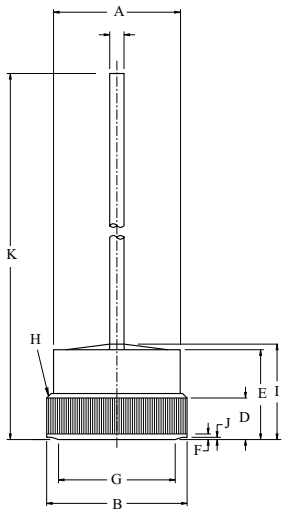
· Average Forward Current : I_O=50A.

· Repetive Peak Reverse Voltage : V_{RRM}=200V

POLARITY

E50A2CBS E50A2CBR

(+ Type) (- Type)



DIM	MILLIMETERS
A	Φ11.5 MAX
B	Φ12.75+0.09-0.00
C	Φ1.3±0.04
D	4.2±0.2
E	8.0±0.2
F	TYP 0.5
G	Φ10.0±0.2
H	0.4±0.1x45°
I	8.5 MAX
J	0.2+0.1
K	28.35±0.5

B-PF

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Average Forward Current	$I_{F(AV)}$	50	A
Peak 1 Cycle Surge Current	I_{FSM}	380 (60Hz)	A
Repetitive Peak Revese Voltage	V_{RRM}	200	V
Junction Temperature	T_j	-40 215	℃
Storage Temperature Range	T_{stg}	-40 215	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	I_{FM}=100A	-	-	1.05	V
Reverse Voltage	V_R	I_R=5mA	200	-	-	V
Reverse Current	I_R	V_R=200V	-	-	50	μA
Transient Thermal Resistance	ΔV_F	I_{FM}=100A, I_M=100mA, Pw=100ms	-	-	80	mV
Reverse Leakage Current Under High Temperature	HI_R	Ta=150℃, V_R=200V	-	-	2.5	mA
Reverse Recovery Time	t_{rr}	I_F=100mA, I_R=100mA	-	-	15	μs
Temperature Resistance	R_{th}	DC total Junction to case	-	-	0.6	℃/W